

MAXIMUM RATINGS

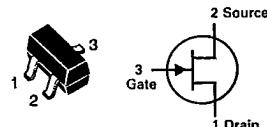
Rating	Symbol	Value	Unit
Drain-Source Voltage	$\pm V_{DS}$	40	V
Drain-Gate Voltage	V_{DG}	40	V
Gate-Source Voltage	V_{GS}	40	V
Forward Gate Current	$I_G(f)$	50	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate,** $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

*FR-5 = $1.0 \times 0.75 \times 0.062$ in.**Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.**DEVICE MARKING**

BSR56L = M4; BSR57L = M5; BSR58L = M6

BSR56L**thru****BSR58L****CASE 318-03, STYLE 10**
SOT-23 (TO-236AB)**JFET**
SWITCHING
TRANSISTORS

N-CHANNEL

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Gate-Source Breakdown Voltage ($I_G = 1.0 \mu\text{Adc}, V_{DS} = 0$)	$V_{(BR)GSS}$	40	—	Vdc
Gate-Reverse Current ($V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$)	I_{GSS}	—	1.0	nA
Gate-Source Cutoff Voltage ($V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ nA}$)	$V_{GS(off)}$	-4.0 -2.0 -0.8	-10 -6.0 -4.0	V

ON CHARACTERISTICS

Zero-Gate Voltage Drain ($V_{DS} = 15 \text{ V}, V_{GS} = 0$)	BSR56L BSR57L BSR58L	I_{DSS}	50 20 8.0	— 100 80	mA
Drain-Source On Voltage ($I_D = 20 \text{ mA}, V_{GS} = 0$) ($I_D = 10 \text{ mA}, V_{GS} = 0$) ($I_D = 5.0 \text{ mA}, V_{GS} = 0$)	BSR56L BSR57L BSR58L	$V_{DS(on)}$	— — —	0.75 0.5 0.4	Vdc
Static Drain-Source On Resistance ($I_D = 0 \text{ mA dc}, V_{GS} = 0, f = 1.0 \text{ kHz}$)	BSR56L BSR57L BSR58L	$r_{DS(on)}$	— — —	25 40 60	Ohms

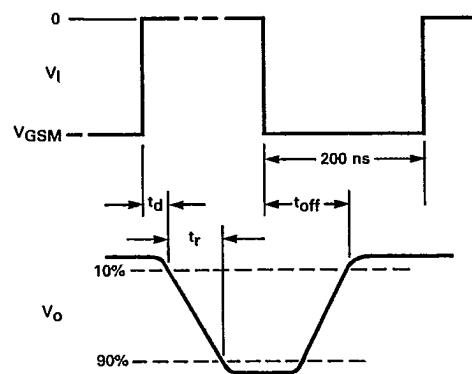
SWITCHING CHARACTERISTICS

Delay Time: $V_{DD} = 10 \text{ V}; V_{GS} = 0$ ($V_{GSM} = 10 \text{ V}, I_D = 20 \text{ mA}$) ($V_{GSM} = 6.0 \text{ V}, I_D = 10 \text{ mA}$) ($V_{GSM} = 4.0 \text{ V}, I_D = 5.0 \text{ mA}$)	BSR56L BSR57L BSR58L	t_d	— — —	6.0 6.0 10	ns
Rise Time: $V_{DD} = 10 \text{ V}; V_{GS} = 0$ ($V_{GSM} = 10 \text{ V}, I_D = 20 \text{ mA}$) ($V_{GSM} = 6.0 \text{ V}, I_D = 10 \text{ mA}$) ($V_{GSM} = 4.0 \text{ V}, I_D = 5.0 \text{ mA}$)	BSR56L BSR57L BSR58L	t_r	— — —	3.0 4.0 10	ns
Turn-Off Time: $V_{DD} = 10 \text{ V}; V_{GS} = 0$ ($V_{GSM} = 10 \text{ V}, I_D = 20 \text{ mA}$) ($V_{GSM} = 6.0 \text{ V}, I_D = 10 \text{ mA}$) ($V_{GSM} = 4.0 \text{ V}, I_D = 5.0 \text{ mA}$)	BSR56L BSR57L BSR58L	t_{off}	— — —	25 50 100	ns

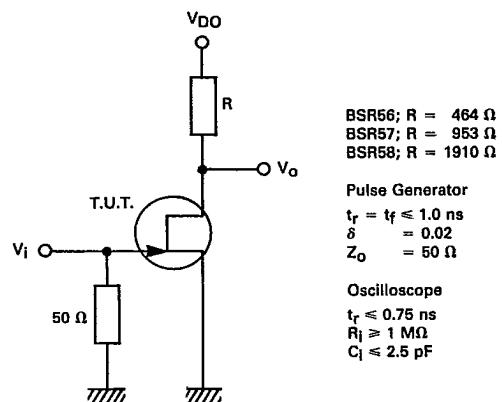
MOTOROLA SMALL-SIGNAL TRANSISTORS, FETs AND DIODES

BSR56L thru BSR58L

T-35-25



SWITCHING TIMES WAVEFORMS



4

MOTOROLA SMALL-SIGNAL TRANSISTORS, FETs AND DIODES